

UF9Z24

Power MOSFET

12A, 55V P-CHANNEL
POWER MOSFET

■ DESCRIPTION

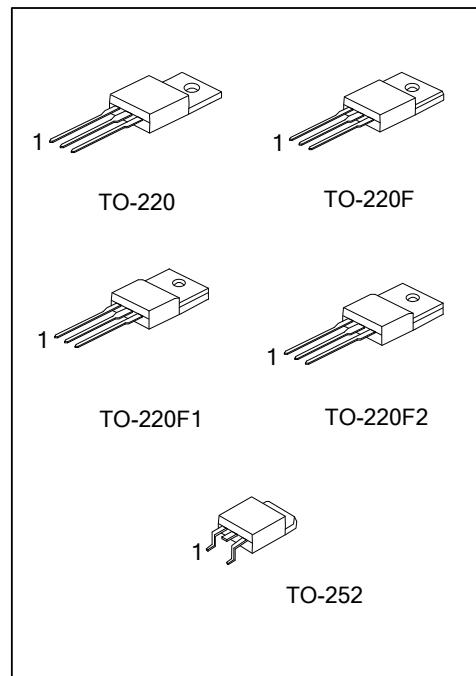
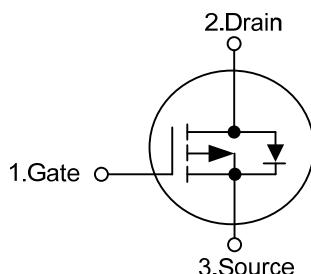
The UTC **UF9Z24** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed, cost-effectiveness and minimum on-state resistance. It can also withstand high energy in the avalanche.

■ FEATURES

* $R_{DS(ON)} < 175\text{m}\Omega$ @ $V_{GS} = -10\text{V}$, $I_D = -12\text{A}$

* High Switching Speed

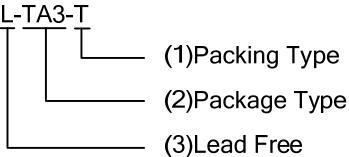
■ SYMBOL



■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|---------------|----------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| UF9Z24L-TA3-T | UF9Z24G-TA3-T | TO-220 | G | D | S | Tube |
| UF9Z24L-TF3-T | UF9Z24G-TF3-T | TO-220F | G | D | S | Tube |
| UF9Z24L-TF1-T | UF9Z24G-TF1-T | TO-220F1 | G | D | S | Tube |
| UF9Z24L-TF2-T | UF9Z24G-TF2-T | TO-220F2 | G | D | S | Tube |
| UF9Z24L-TN3-T | UF9Z24G-TN3-T | TO-252 | G | D | S | Tube |
| UF9Z24L-TN3-R | UF9Z24G-TN3-R | TO-252 | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|--|--|
| UF9Z24L-TA3-T  | (1) T: Tube, R: Tape Reel (2) TA3: TO-220, TN3: TO-252 (3) L: Lead Free, G: Halogen Free |
|--|--|

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | | | SYMBOL | RATINGS | UNIT |
|---|------------------|------------------------|-----------|----------|------------------|
| Drain-Source Voltage | | | V_{DSS} | -55 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 20 | V |
| Drain Current | Continuous | $T_c=25^\circ\text{C}$ | I_D | -12 | A |
| | Pulsed | | I_{DM} | -48 | A |
| Single Pulsed Avalanche Current ($L=0.1\text{mH}$) | | | I_{AS} | -7.2 | A |
| Single Pulsed Avalanche Energy ($L=0.1\text{mH}$)(Note 1) | | | E_{AS} | 96 | mJ |
| Power Dissipation | TO-220 | | P_D | 38 | W |
| | TO-220F/TO-220F1 | | | 23 | W |
| | TO-220F2 | | | 25 | W |
| | TO-252 | | | 27 | W |
| Junction Temperature | | | T_J | +150 | $^\circ\text{C}$ |
| Storage Temperature | | | T_{STG} | -55~+150 | $^\circ\text{C}$ |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---------------------|-------------------|---------------|---------|--------------------|
| Junction to Ambient | TO-220/TO-220F | θ_{JA} | 62 | $^\circ\text{C/W}$ |
| | TO-220F1/TO-220F2 | | 110 | $^\circ\text{C/W}$ |
| | TO-252 | | 3.3 | $^\circ\text{C/W}$ |
| Junction to Case | TO-220 | θ_{JC} | 5.5 | $^\circ\text{C/W}$ |
| | TO-220F/TO-220F1 | | 5 | $^\circ\text{C/W}$ |
| | TO-220F2 | | 4.6 | $^\circ\text{C/W}$ |
| | TO-252 | | | |

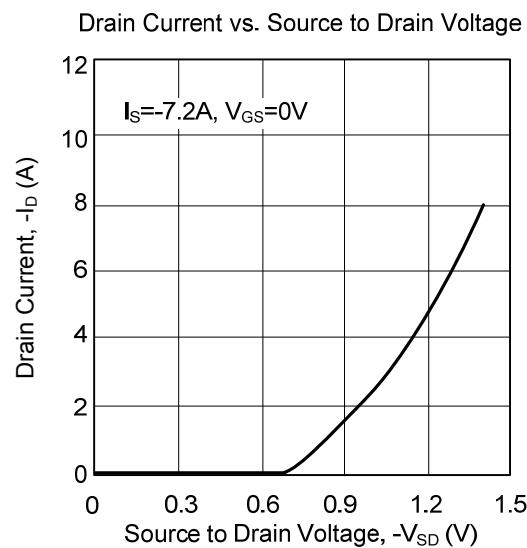
Notes: 1. Duty cycle≤1 %.

■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--------------------------|--|------|-----|-------|---------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $I_D=-250\mu\text{A}, V_{GS}=0\text{V}$ | -55 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS}=-55\text{V}, V_{GS}=0\text{V}$ | | | -25 | μA |
| Gate-Source Leakage Current | Forward | $V_{GS}=+20\text{V}$ | | | +100 | nA |
| | Reverse | $V_{GS}=-20\text{V}$ | | | -100 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | $V_{GS(\text{TH})}$ | $V_{DS}=V_{GS}, I_D=-250\mu\text{A}$ | -2.0 | | -4.0 | V |
| Static Drain-Source On-State Resistance | $R_{DS(\text{ON})}$ | $V_{GS}=-10\text{V}, I_D=-12\text{A}$ (Note 1) | | | 0.175 | Ω |
| On State Drain Current (Note 1) | $I_{D(\text{ON})}$ | $V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$ | -12 | | | A |
| DYNAMIC PARAMETERS (Note 2) | | | | | | |
| Input Capacitance | C_{ISS} | $V_{GS}=0\text{V}, V_{DS}=-25\text{V}, f=1.0\text{MHz}$ (Note 2) | | 350 | | pF |
| Output Capacitance | C_{OSS} | | | 170 | | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | 92 | | pF |
| SWITCHING PARAMETERS | | | | | | |
| Total Gate Charge | Q_G | $V_{GS}=-10\text{V}, V_{DS}=-44\text{V}, I_D=-7.2\text{A}$ (Note 3) | | 52 | | nC |
| Gate to Source Charge | Q_{GS} | | | 6.6 | | nC |
| Gate to Drain Charge | Q_{GD} | | | 12 | | nC |
| Turn-ON Delay Time | $t_{D(\text{ON})}$ | $V_{DD}=-28\text{V}, I_D=-7.2\text{A}, R_G=24\Omega, R_D=3.7\Omega$ (Note 3) | | 13 | | ns |
| Rise Time | t_R | | | 55 | | ns |
| Turn-OFF Delay Time | $t_{D(\text{OFF})}$ | | | 23 | | ns |
| Fall-Time | t_F | | | 37 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS (Note 2) | | | | | | |
| Maximum Body-Diode Continuous Current | I_S | | | | -12 | A |
| Maximum Body-Diode Pulsed Current | I_{SM} | | | | -48 | A |
| Drain-Source Diode Forward Voltage | V_{SD} | $I_F=-12\text{A}, V_{GS}=0\text{V}$ (Note 1) | | | -1.6 | V |

- Notes: 1. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 2. Guaranteed by design, not subject to production testing.
 3. Independent of operating temperature.

- TYPICAL CHARACTERISTICS



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